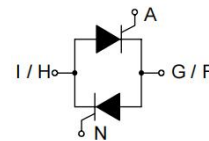


PRODUCT FEATURES

- Base plate: Copper
- Glass passivation thyristor chips
- Low Leakage Current
- Internally DBC isolated
- Advanced power cycling


APPLICATIONS

- Softstart AC motor control
- Temperature control
- AC power control
- Power converte
- Lighting and temperature control


ABSOLUTE MAXIMUM RATINGS(T_C =25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Values	Unit
V _{RRM}	Maximum Repetitive Reverse Voltage	T _{vj} =125°C	1600	V
V _{DRM}	Maximum repetitive peak off-state voltage			
V _{RSM}	Non-Repetitive Reverse Voltage	T _{vj} =125°C	1700	V
V _{DSM}	Non-repetitive peak off-state voltage			
I _{RRM}	Maximum Repetitive Reverse Current	T _{vj} =125°C	5	mA
I _{DRM}	Maximum repetitive peak off-state Current			
I _{T(AV)}	Mean On-state Current	T _C =85°C	80	A
I _{T(RMS)}	RMS Current	T _C =85°C, sin180°	125	
I _{RMS}	Module	T _C =85°C	175	
I _{TSM}	Non Repetitive Surge Peak On-state Current	10ms, T _j =25°C	1500	
I ² t	For Fusing	10ms, T _j =25°C	11000	A ² S
V _{TM}	Peak on-state voltage	I _{TM} =240A	1.67	V
dv/dt	critical rate of rise of off-state voltage	V _D =2/3V _{DRM} Gate Open T _j =125°C	1000	V/us
I _{GT}	gate trigger current max.		100	mA
V _{GT}	gate trigger voltage max.		1.3	V
I _H	gate trigger current		200	mA
I _L	latching current		350	mA
V _{iso}	AC 50Hz RMS 1min		2500	V
T _J	Junction Temperature		-40 to +150	°C
T _{STG}	Storage Temperature Range		-40 to +150	
R _{thJC}	Junction to Case Thermal Resistance(Per thyristor chip)		0.45	°C /W

V _{To}	For power-loss calculations only	0.95	V
r _T		3.9	mΩ

Outlines

